

IN THE CLAIMS

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1. (Amended) A semiconductor device comprising:

(a) a semiconductor substrate having a first surface and a second surface;

(b) an active region [formed] on the first surface of the substrate;

(c) a first semiconductor element [formed on] in the active region, including

first and second channel regions [formed so that the] having width directions [of the channel regions are] substantially perpendicular to each other,

a first source electrode and a first drain electrode, [which are formed] adjacent to the first and second channel regions and opposing [to] each other with the first and second channel regions therebetween, and [which are] in ohmic contact with the active region, and

a first gate electrode [which is formed] on the first and second channel regions and along the first source electrode and the first drain electrode, and [which is] bent at at least one bending position; and

(d) a second semiconductor element [formed] on the active region [so as to be] adjacent to the first semiconductor element, including

third and fourth channel regions [which are formed] adjacent to the first and second channel regions, respectively, with one of the first source electrode [or] and the first drain electrode therebetween,

one of a second source electrode [or] and a second drain electrode [which is formed] opposing the first drain electrode or the first source electrode [through]

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across the third and fourth channel regions, and [which is] in ohmic contact with the [surface of the] active region, and

a second gate electrode [which is formed] on the third and fourth channel regions and along one of the second source electrode [or] and the second drain electrode, and [which is] bent at at least one bending position.

Claim 2 (Amended), line 3, delete "composed of";

line 5, change "are arranged" to --lie--;

line 6, delete "in";

change "the" to --a--.

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3. (Amended) The semiconductor device according to claim 1, further comprising:

a source-drawing wire [which is formed] on the first source electrode and along the first source electrode;

a source common wire connected to the source-drawing wire;

a drain-drawing wire [which is formed] on the first drain electrode and along the first drain electrode;

a drain common wire connected to the drain-drawing wire; and

a gate common wire connected to the first gate electrode, wherein the drain common wire is [formed opposing] opposite the source common wire and the gate common wire [through] across the active region, and wherein the source-drawing wire is

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Claim 9 (Amended), line 3, delete "formed in";

change "with" to --to--;

line 4, change "which is formed on the" to --at a--;

line 5, change "the" (second occurrence) to --a--.

Claim 10 (Amended), line 2, change "made of" to --an--;

line ⁹4, after "compound" insert --semiconductor material--.

Claim 11 (Amended), line 3, after "share" insert --one of--;

change "or" to --and--.

Claim 12 (Amended), line 2, change "in" to --at--;

lines 2-3, change "vertical direction" to --right angle--;

line 3, change "the" to --a--.

Claim 13 (Amended), line 2, change "the" (first occurrence) to --an--;

change "by the" to --between a--;

line 3, change "the" (first occurrence) to --a--.

14. (Amended) A process for manufacturing a semiconductor device, comprising

[the steps of]:

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[setting] providing a semiconductor substrate having a first surface and a second surface,

forming an active region on the first surface of the substrate,

forming a first channel region and a second channel region [on] in the active region so that [the] width directions of [both channels] the first and second channel regions are substantially perpendicular to each other,

forming a gate electrode on the first and second channel regions so that the gate electrode bends at a bending position and extends along the first and second channel regions, and

forming a source electrode and a drain electrode substantially [in] parallel [with] to the gate electrode so that the source electrode and the drain electrode oppose [to] each other [through] across the first and second channel regions.

Claim 15 (Amended), line 2, delete "the step of".

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16. (Amended) The process according to claim 14, further comprising [the steps of]:

forming a conductive film on the second surface of the semiconductor substrate,

and

forming a via-hole penetrating the semiconductor substrate and electrically connecting the source electrode to the conductive film through the via-hole [penetrating the semiconductor substrate].